said step of outputting said first data overlaps with said step of reading second data.

16. · A method for writing data to a non-volatile semiconductor memory device, said non-volatile semiconductor memory device including a memory cell storing first and second data, said first and second registers, said method comprising the steps of:

storing in said first register said first data input from the outside of said non-volatile semiconductor memory device;

writing said first data stored in said first register to said memory cell;

storing in said second register said second data input from the outside of said non-volatile semiconductor memory device; and

writing said second data stored in said second register to said memory cell.

17. The method according to claim 16, wherein

said step of writing said first data overlaps with said step of storing said second data. --

REMARKS

Entry of the above amendments, and consideration on the merits in due course, are respectfully requested.

To the extent necessary, a petition for an extension of time under 37 C.F.R. 1.136 is hereby made. Please charge any shortage in fees due in connection with the filing of this

paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

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